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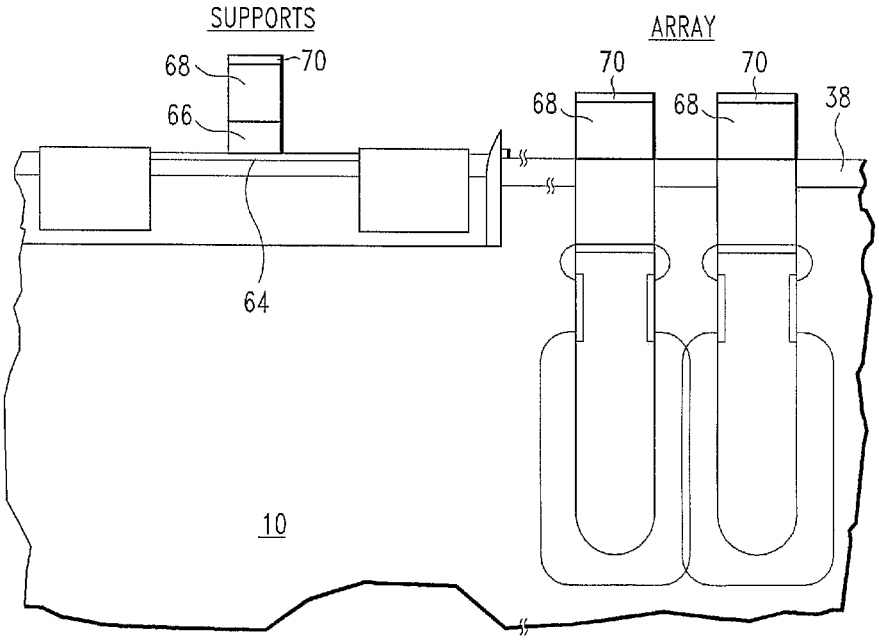
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(54) Title: HIGH PERFORMANCE EMBEDDED DRAM TECHNOLOGY WITH STRAINED SILICON



(57) Abstract: Semiconductor devices are fabricated in a strained layer region and strained layer-free region of the same substrate. A first semiconductor device, such as a memory cell, e.g. a deep trench storage cell, is formed in a strained layer-free region of the substrate. A strained layer region is selectively formed in the same substrate. A second semiconductor device (66, 68, 70), such as an FET, e.g. an MOSFET logic device, is formed in the strained layer region.

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